

SN74CB3Q3253 双 4 选 1 FET 多路复用器 - 多路信号分离器

2.5V – 3.3V 低电压高带宽总线开关

1 特性

- 高带宽数据路径（高达 500 MHz）⁽¹⁾
 - 可耐受 5V 电压和支持器件上电或断电的 I/O 端口
 - 在运行范围内具有平缓的低通态电阻 (r_{on}) 特性 (r_{on} 典型值 = 4Ω)
 - 支持在数据 I/O 端口进行轨至轨开关
 - 3.3V V_{CC} 时，开关范围为 0 至 5V
 - 2.5V V_{CC} 时，开关范围为 0 至 3.3V
 - 具有接近零传播延迟的双向数据流
 - 低输入/输出电容可最大限度地减小负载和信号失真 ($C_{io(OFF)}$ 典型值 = 3.5 pF)
 - 快速开关频率 (f_{OE} 最大值 = 20MHz)
 - 数据与控制输入提供下冲钳位二极管
 - 低功耗 (I_{CC} 典型值 = 0.6mA)
 - V_{CC} 工作电压范围为 2.3V 至 3.6V
 - 数据 I/O 支持 0V 至 5V 信号电平 (0.8V、1.2V、1.5V、1.8V、2.5V、3.3V、5V)
 - 控制输入可由 TTL 或 5V 和 3.3V CMOS 输出驱动
 - I_{off} 支持局部关断模式运行
 - 锁断性能超过 100mA，符合 JESD 78 II 类规范的要求
 - ESD 性能测试符合 JESD 22 标准
 - 2000V 人体放电模型 (A114-B, II 类)
 - 1000V 充电器件模型 (C101)
 - 支持数字和模拟应用：USB 接口、差分信号接口总线隔离、低失真信号闸控
- ⁽¹⁾ 有关 CB3Q 系列器件性能特点的更多信息，请参考 TI 应用报告 CBT-C、CB3T 和 CB3Q 信号开关系列，(SCDA008)。

2 应用

- 视频广播：基于 IP 的多格式转码器
- 视频通信系统

3 说明

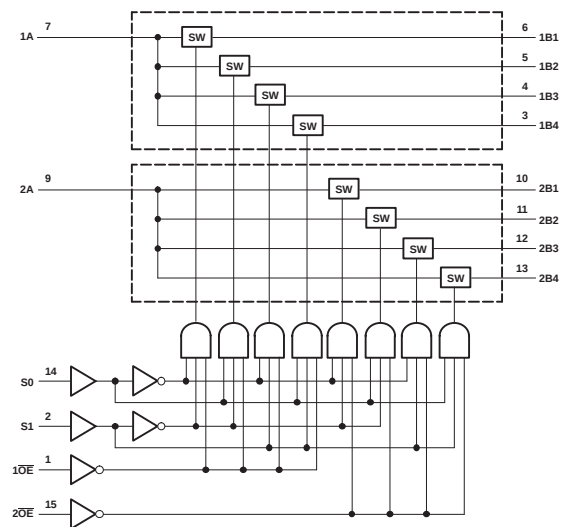
SN74CB3Q3253 器件是一款高带宽 FET 总线开关，此开关利用一个电荷泵来提升通道晶体管的栅极电压，从而提供一个平缓的低通态电阻 (r_{on})。平缓的低通态电阻可实现最小传播延迟，并且支持在数据输入/输出 (I/O) 端口上进行轨至轨开关。

器件信息

器件编号	封装	封装尺寸 (标称值)
SN74CB3Q3253DBQ	SSOP (16)	4.90mm × 3.90mm
SN74CB3Q3253DGV	TVSOP (16)	3.60mm × 4.40mm
SN74CB3Q3253RGY	VQFN (16)	4.00mm × 3.50mm
SN74CB3Q3253PW	TSSOP (16)	5.00mm × 4.40mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

逻辑图 (正逻辑)



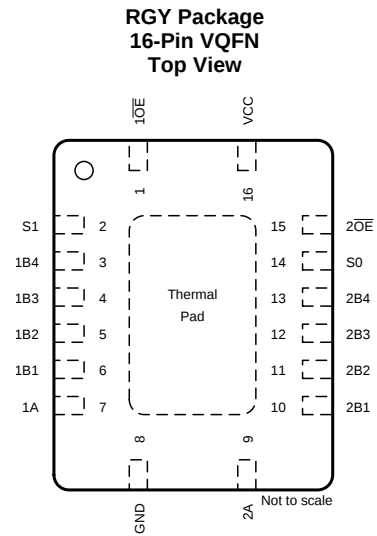
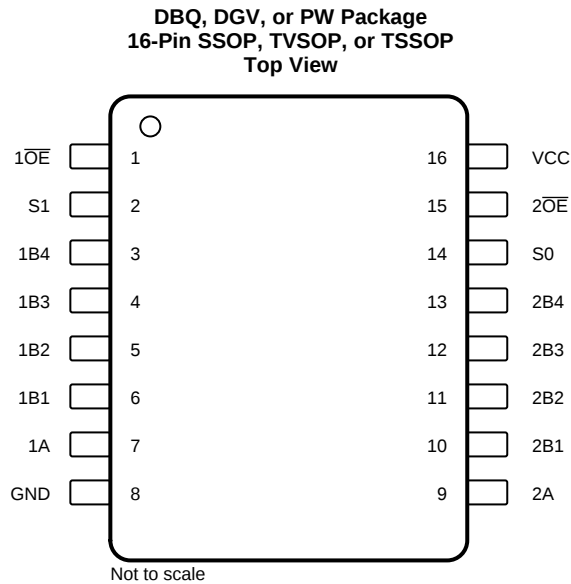
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4 修订历史记录

Changes from Revision B (June 2015) to Revision C	Page
• Changed the pinout image appearance	3
• Updated the <i>Thermal Information</i> table	5
Changes from Revision A (November 2003) to Revision B	Page
• 删除了订购信息表。	1
• 添加了应用、器件信息表、引脚配置和功能部分、贮存条件表、ESD 额定值表、特性说明部分、器件功能模式、应用和实施部分、电源相关建议部分、布局部分、器件和文档支持部分以及机械、封装和可订购信息部分	1

5 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
1OE	1	I	Output Enable 1 Active-Low
S1	2	I	Select Pin 1
1B4	3	I/O	Channel 1 I/O 4
1B3	4	I/O	Channel 1 I/O 3
1B2	5	I/O	Channel 1 I/O 2
1B1	6	I/O	Channel 1 I/O 1
1A	7	I/O	Channel 1 common
GND	8	—	Ground
2A	9	I/O	Channel 2 common
2B1	10	I/O	Channel 2 I/O 1
2B2	11	I/O	Channel 2 I/O 2
2B3	12	I/O	Channel 2 I/O 3
2B4	13	I/O	Channel 2 I/O 4
S0	14	I	Select Pin 0
2OE	15	I	Output Enable 2 Active-Low
VCC	16	—	Power

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	−0.5	4.6	V
V _{IN}	Control input voltage ⁽²⁾⁽³⁾	−0.5	7	V
V _{I/O}	Switch I/O voltage ⁽²⁾⁽³⁾⁽⁴⁾	−0.5	7	V
I _{IK}	Control input clamp current	V _{IN} < 0	−50	mA
I _{I/O}	I/O port clamp current	V _{I/O} < 0	−50	mA
I _{I/O}	ON-state switch current ⁽⁵⁾		±64	mA
	Continuous current through V _{CC} or GND		±100	mA
T _{stg}	Storage temperature	−65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with respect to ground, unless otherwise specified.

(3) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

(4) V_I and V_O are used to denote specific conditions for V_{I/O}.

(5) I_I and I_O are used to denote specific conditions for I_{I/O}.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	+2000
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	+1000

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	2.3	3.6	V
V _{IH}	High-level control input voltage	V _{CC} = 2.3 V to 2.7 V	1.7	5.5
		V _{CC} = 2.7 V to 3.6 V	2	5.5
V _{IL}	Low-level control input voltage	V _{CC} = 2.3 V to 2.7 V	0	0.7
		V _{CC} = 2.7 V to 3.6 V	0	0.8
V _{I/O}	Data input/output voltage	0	5.5	V
T _A	Operating free-air temperature	−40	85	°C

(1) All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, (SCBA004).

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74CB3Q3253				UNIT
		DBQ (SSOP)	DGV (TVSOP)	PW (TSSOP)	RGY (VQFN)	
		16 PINS	16 PINS	16 PINS	16 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	114.3	126	112.7	45.7	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	65.4	51.3	47.5	59.6	°C/W
R _{θJB}	Junction-to-board thermal resistance	56.8	57.8	57.85	23.3	°C/W
ψ _{JT}	Junction-to-top characterization parameter	18.3	5.9	6	2.2	°C/W
ψ _{JB}	Junction-to-board characterization parameter	56.4	57.3	57.3	23.4	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	n/a	n/a	n/a	11.5	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)⁽¹⁾

PARAMETER		TEST CONDITIONS		MIN	TYP ⁽²⁾	MAX	UNIT
V _{IK}		V _{CC} = 3.6 V,	I _I = –18 mA			–1.8	V
I _{IN}	Control inputs	V _{CC} = 3.6 V,	V _{IN} = 0 to 5.5 V			±1	μA
I _{OZ} ⁽³⁾		V _{CC} = 3.6 V,	V _O = 0 to 5.5 V, V _I = 0, Switch OFF, V _{IN} = V _{CC} or GND			±1	μA
I _{off}		V _{CC} = 0,	V _O = 0 to 5.5 V, V _I = 0			1	μA
I _{CC}		V _{CC} = 3.6 V,	I _{I/O} = 0, Switch ON or OFF, V _{IN} = V _{CC} or GND		0.6	2	mA
ΔI _{CC} ⁽⁴⁾	Control inputs	V _{CC} = 3.6 V,	One input at 3 V, Other inputs at V _{CC} or GND			30	μA
I _{CCD} ⁽⁵⁾	Per control input	V _{CC} = 3.6 V, Control input switching at 50% duty cycle	A and B ports open, OE input S input		0.15 0.04	0.16 0.05	mA/ MHz
C _{in}	Control inputs	V _{CC} = 3.3 V,	V _{IN} = 5.5 V, 3.3 V, or 0		2.5	3.5	pF
C _{io(OFF)}	A port	V _{CC} = 3.3 V,	Switch OFF, V _{IN} = V _{CC} or GND, V _{I/O} = 5.5 V, 3.3 V, or 0		8	11	pF
	B port	V _{CC} = 3.3 V,	Switch OFF, V _{IN} = V _{CC} or GND, V _{I/O} = 5.5 V, 3.3 V, or 0		3.5	4.5	pF
C _{io(ON)}		V _{CC} = 3.3 V,	Switch ON, V _{IN} = V _{CC} or GND, V _{I/O} = 5.5 V, 3.3 V, or 0		13	17	pF
r _{on} ⁽⁶⁾		V _{CC} = 2.3 V, TYP at V _{CC} = 2.5 V	V _I = 0, I _O = 30 mA		4	10	Ω
			V _I = 1.7 V, I _O = –15 mA		4.5	11	
		V _{CC} = 3 V	V _I = 0, I _O = 30 mA		3.5	8	
			V _I = 2.4 V, I _O = –15 mA		4	10	

- (1) V_{IN} and I_{IN} refer to control inputs. V_I, V_O, I_I, and I_O refer to data pins.
(2) All typical values are at V_{CC} = 3.3 V (unless otherwise noted), T_A = 25°C.
(3) For I/O ports, the parameter I_{OZ} includes the input leakage current.
(4) This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V_{CC} or GND.
(5) This parameter specifies the dynamic power-supply current associated with the operating frequency of a single control input (see [Figure 2](#)).
(6) Measured by the voltage drop between the A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see [Figure 3](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		UNIT
			MIN	MAX	MIN	MAX	
$f_{\overline{OE}} \text{ or } f_S^{(1)}$	$\overline{OE}$ or S	A or B		10		20	MHz
$t_{pd}^{(2)}$	A or B	B or A		0.12		0.18	ns
$t_{pd(s)}$	S	A	1.5	6.7	1.5	5.9	ns
t_{en}	S	B	1.5	6.7	1.5	5.9	ns
	$\overline{OE}$	A or B	1.5	6.7	1.5	5.9	
t_{dis}	S	B	1	6.1	1	6.1	ns
	$\overline{OE}$	A or B	1	6.1	1	6.1	

(1) Maximum switching frequency for control input ($V_O > V_{CC}$, $V_I = 5 \text{ V}$, $R_L \geq 1 \text{ M}\Omega$, $C_L = 0$).

(2) The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

6.7 Typical Characteristics

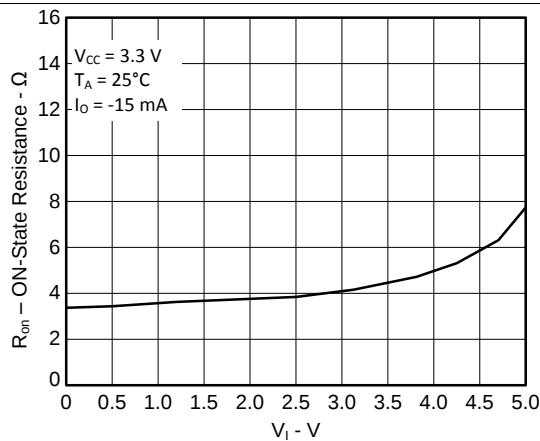


Figure 1. Typical r_{on} vs V_I , $V_{CC} = 3.3 \text{ V}$ and $I_O = -15 \text{ mA}$

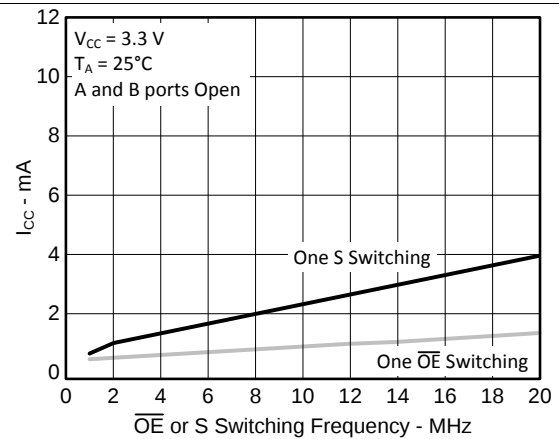
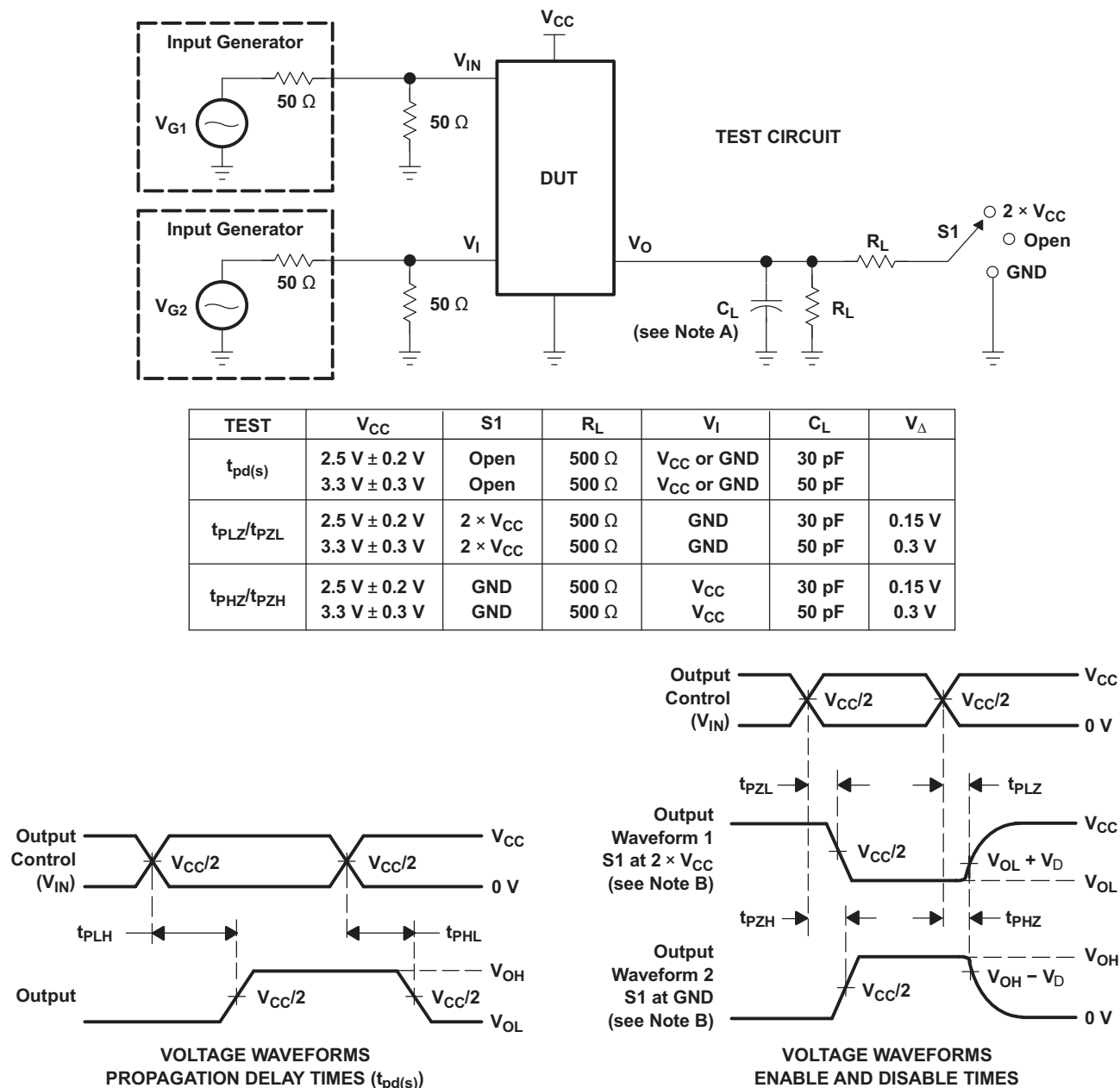


Figure 2. Typical I_{CC} vs $\overline{OE}$ or S Switching Frequency, $V_{CC} = 3.3 \text{ V}$

7 Parameter Measurement Information



- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 2.5\text{ ns}$, $t_f \leq 2.5\text{ ns}$.
 - The outputs are measured one at a time, with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{en} .
 - t_{PLH} and t_{PHL} are the same as $t_{pd(s)}$. The t_{pd} propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
 - All parameters and waveforms are not applicable to all devices.

Figure 3. Test Circuit and Voltage Waveforms

8 Detailed Description

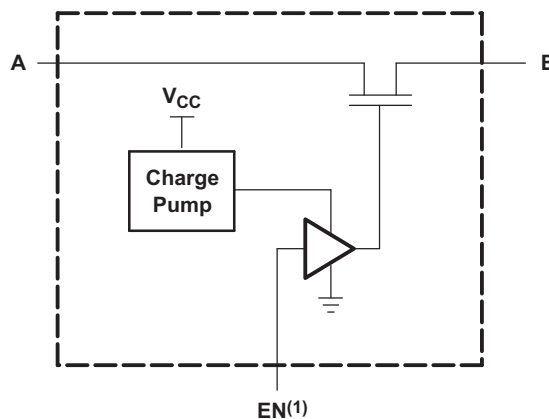
8.1 Overview

The SN74CB3Q3253 device is a high-bandwidth FET bus switch using a charge pump to elevate the gate voltage of the pass transistor, providing a low and flat ON-state resistance (r_{on}). The low and flat ON-state resistance allows for minimal propagation delay and supports rail-to-rail switching on the data input/output (I/O) ports. The device also features low data I/O capacitance to minimize capacitive loading and signal distortion on the data bus. Specifically designed to support high-bandwidth applications, the SN74CB3Q3253 device provides an optimized interface solution ideally suited for broadband communications, networking, and data-intensive computing systems.

The SN74CB3Q3253 device is organized as two 1-of-4 multiplexers/demultiplexers with separate output-enable (1OE, 2OE) inputs. The select (S0, S1) inputs control the data path of each multiplexer/demultiplexer. When OE is low, the associated multiplexer/demultiplexer is enabled, and the A port is connected to the B port, allowing bidirectional data flow between ports. When OE is high, the associated multiplexer/demultiplexer is disabled, and a high-impedance state exists between the A and B ports.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry prevents damaging current backflow through the device when it is powered down. The device has isolation during power off.

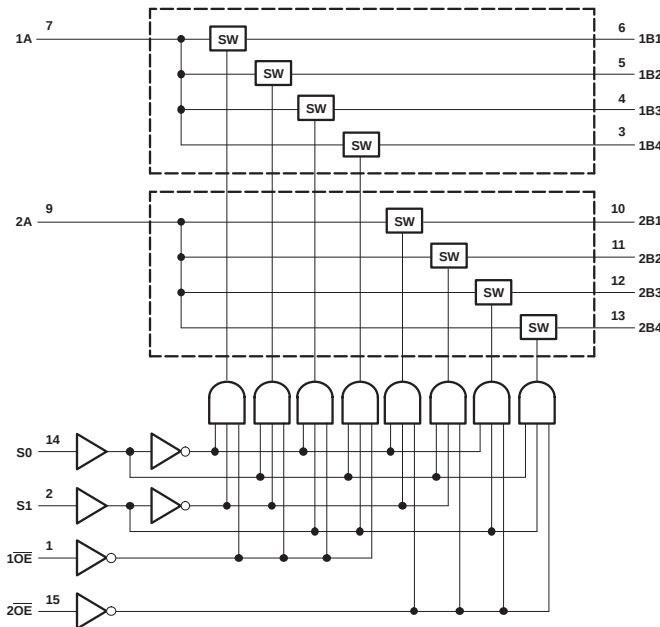
To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.



(1) EN is the internal enable signal applied to the switch.

Figure 4. Simplified Schematic, Each FET Switch (SW)

8.2 Functional Block Diagram



8.3 Feature Description

The SN74CB3Q3253 device has a high-bandwidth data path (up to 500 MHz) and has 5-V tolerant I/Os with the device powered up or powered down. It also has low and flat ON-state resistance (r_{on}) characteristics over operating range ($r_{on} = 4 \Omega$ Typical)

This device also has rail-to-rail switching on data I/O ports for 0- to 5-V switching with 3.3-V V_{CC} and 0- to 3.3-V switching with 2.5-V V_{CC} as well as bidirectional data flow with near-zero propagation delay and low input and output capacitance that minimizes loading and signal distortion ($C_{io(OFF)} = 3.5$ pF Typical)

The SN74CB3Q3253 also provides a fast switching frequency ($f_{OE} = 20$ MHz Maximum) with data and control inputs that provide undershoot clamp diodes as well as low power consumption ($I_{CC} = 0.6$ mA Typical)

The V_{CC} operating range is from 2.3 V to 3.6 V and the data I/Os support 0- to 5-V signal levels of (0.8-V, 1.2-V, 1.5-V, 1.8-V, 2.5-V, 3.3-V, 5-V)

The control inputs can be driven by TTL or 5-V and 3.3-V CMOS outputs as well as I_{off} Supports Partial-Power-Down Mode Operation

8.4 Device Functional Modes

Table 1 lists the functional modes of the SN74CB3Q3253.

**Table 1. Function Table
(Each Multiplexer/Demultiplexer)**

INPUTS			INPUT/OUTPUT	FUNCTION
$\overline{OE}$	S1	S0	A	
L	L	L	B1	A port = B1 port
L	L	H	B2	A port = B2 port
L	H	L	B3	A port = B3 port
L	H	H	B4	A port = B4 port
H	X	X	Z	Disconnect

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74CB3Q3253 device can be used to multiplex and demultiplex up to 4 channels simultaneously in a 2:1 configuration.

9.2 Typical Application

The application shown here is a 4-bit bus being multiplexed between two devices. the $\overline{OE}$ and S pins are used to control the chip from the bus controller. This is a very generic example, and could apply to many situations. If an application requires less than 4 bits, be sure to tie the A side to either high or low on unused channels.

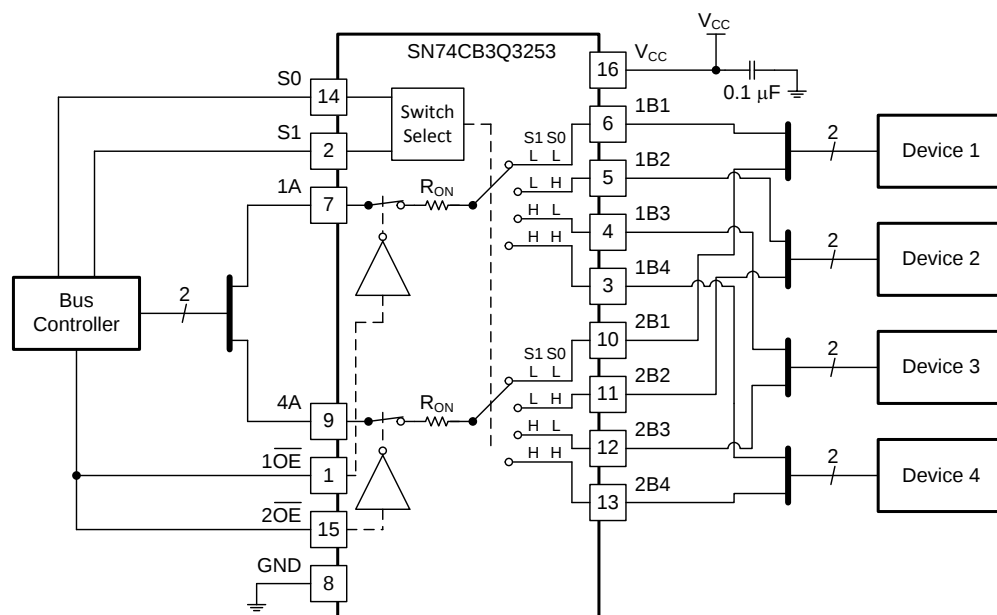


Figure 5. Typical Application of the SN74CB3Q3253

9.2.1 Design Requirements

The 0.1-μF capacitor should be placed as close as possible to the device.

9.2.2 Detailed Design Procedure

- Recommended Input Conditions:
 - For specified high and low levels, see V_{IH} and V_{IL} in [Recommended Operating Conditions](#).
 - Inputs and outputs are overvoltage tolerant allowing them to go as high as 4.6 V at any valid V_{CC} .
- Recommended Output Conditions:
 - Load currents should not exceed ± 128 mA per channel.
- Frequency Selection Criterion:
 - Maximum frequency tested is 500 MHz.
 - Added trace resistance and capacitance can reduce maximum frequency capability; use layout practices as directed in [Layout](#).

Typical Application (continued)

9.2.3 Application Curve

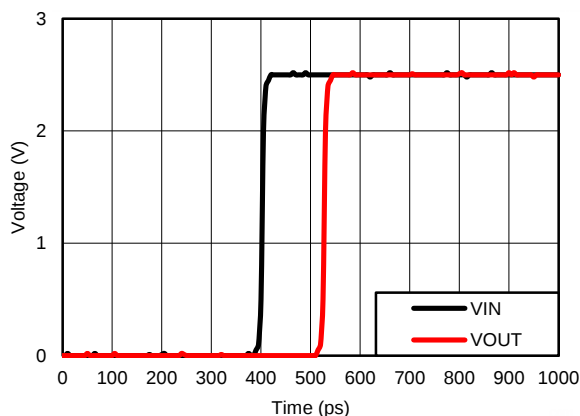


Figure 6. Propagation Delay (t_{pd}) Simulation Result at $V_{CC} = 2.5$ V

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the [Absolute Maximum Ratings](#) table.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μ F bypass capacitor is recommended. If multiple pins are labeled V_{CC} , then a 0.01- μ F or 0.022- μ F capacitor is recommended for each V_{CC} because the V_{CC} pins are tied together internally. For devices with dual-supply pins operating at different voltages, for example V_{CC} and V_{DD} , a 0.1- μ F bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1 μ F and 1 μ F are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

11 Layout

11.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self-inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. [Figure 7](#) shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

11.2 Layout Example

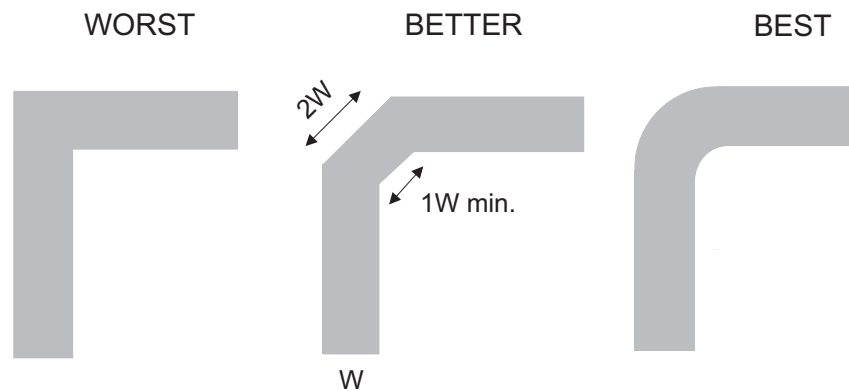


Figure 7. Trace Example

12 器件和文档支持

12.1 文档支持

12.1.1 相关文档

请参阅如下相关文档：

- 《CMOS 输入缓慢变化或悬空的影响》，[SCBA004](#)
- 选择合适的德州仪器 (TI) 信号开关，[SZZA030](#)

12.2 接收文档更新通知

要接收文档更新通知，请导航至 [TI.com.cn](#) 上的器件产品文件夹。单击右上角的通知我 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

12.3 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商“按照原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

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设计支持 TI 参考设计支持 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

12.4 商标

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12.5 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

12.6 术语表

[SLYZ022](#) — TI 术语表。

这份术语表列出并解释术语、缩写和定义。

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此产品说明书的浏览器版本，请参阅左侧的导航栏。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74CB3Q3253DBQR	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253DBQR.A	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253DBQR.B	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253DBQRG4.A	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253DBQRG4.B	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253DGVR	Active	Production	TVSOP (DGV) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253DGVR.B	Active	Production	TVSOP (DGV) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253DGVRG4.B	Active	Production	TVSOP (DGV) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253PW	Obsolete	Production	TSSOP (PW) 16	-	-	Call TI	Call TI	-40 to 85	BU253
SN74CB3Q3253PWR	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253PWR.A	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253PWR.B	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253RGYR	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253RGYR.A	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253RGYR.B	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253RGYRG4.A	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253RGYRG4.B	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74CB3Q3253DBQR	SSOP	DBQ	16	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
SN74CB3Q3253DGVR	TVSOP	DGV	16	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CB3Q3253PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CB3Q3253RGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74CB3Q3253DBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
SN74CB3Q3253DGVR	TVSOP	DGV	16	2000	367.0	367.0	35.0
SN74CB3Q3253PWR	TSSOP	PW	16	2000	367.0	367.0	35.0
SN74CB3Q3253RGYR	VQFN	RGY	16	3000	367.0	367.0	35.0



4220204/A 02/2017

NOTES:

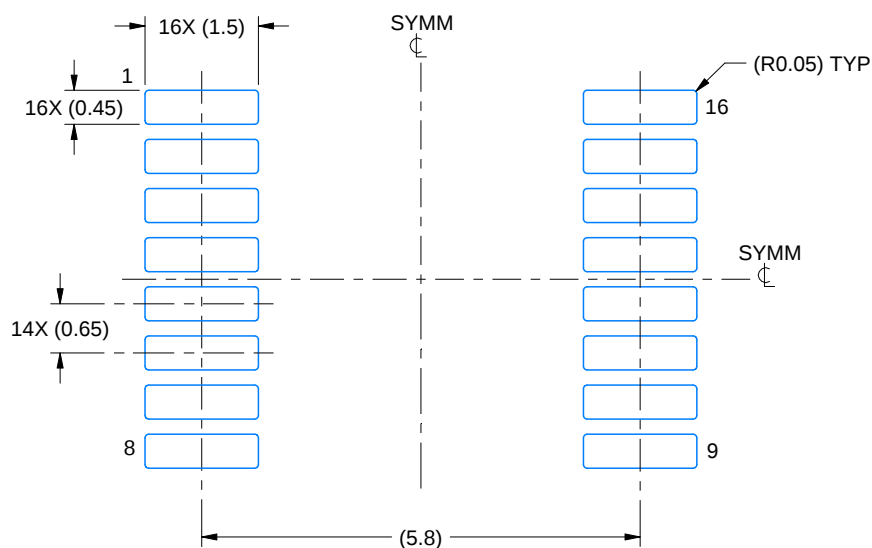
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

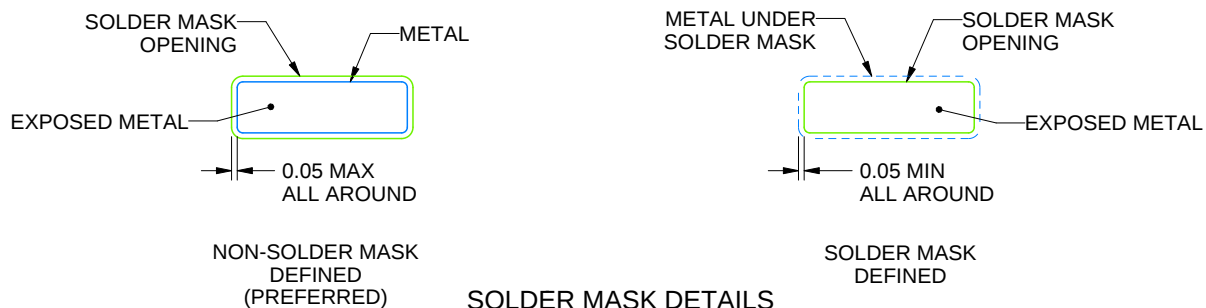
PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



SOLDER MASK DETAILS

4220204/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

DGV (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

24 PINS SHOWN



- NOTES: A. All linear dimensions are in millimeters.
 B. This drawing is subject to change without notice.
 C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
 D. Falls within JEDEC: 24/48 Pins – MO-153
 14/16/20/56 Pins – MO-194



PACKAGE OUTLINE

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



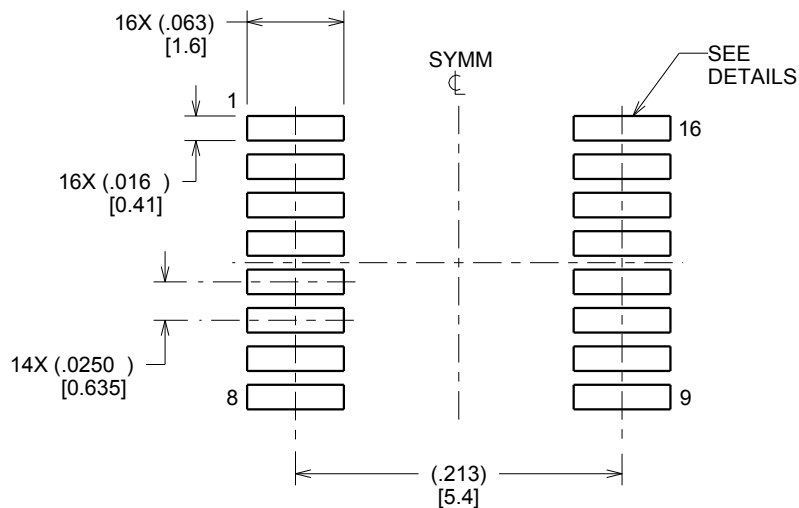
1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 inch, per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MO-137, variation AB.

EXAMPLE BOARD LAYOUT

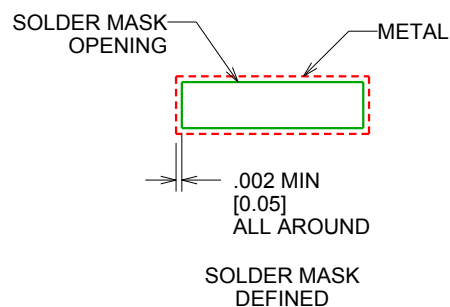
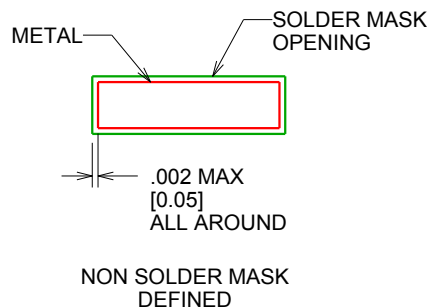
DBQ0016A

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



LAND PATTERN EXAMPLE
SCALE:8X



SOLDER MASK DETAILS

4214846/A 03/2014

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

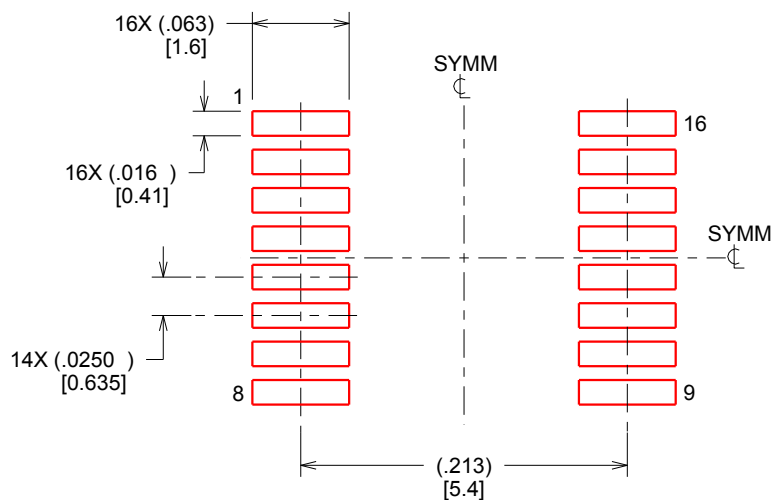
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBQ0016A

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.127 MM] THICK STENCIL
SCALE:8X

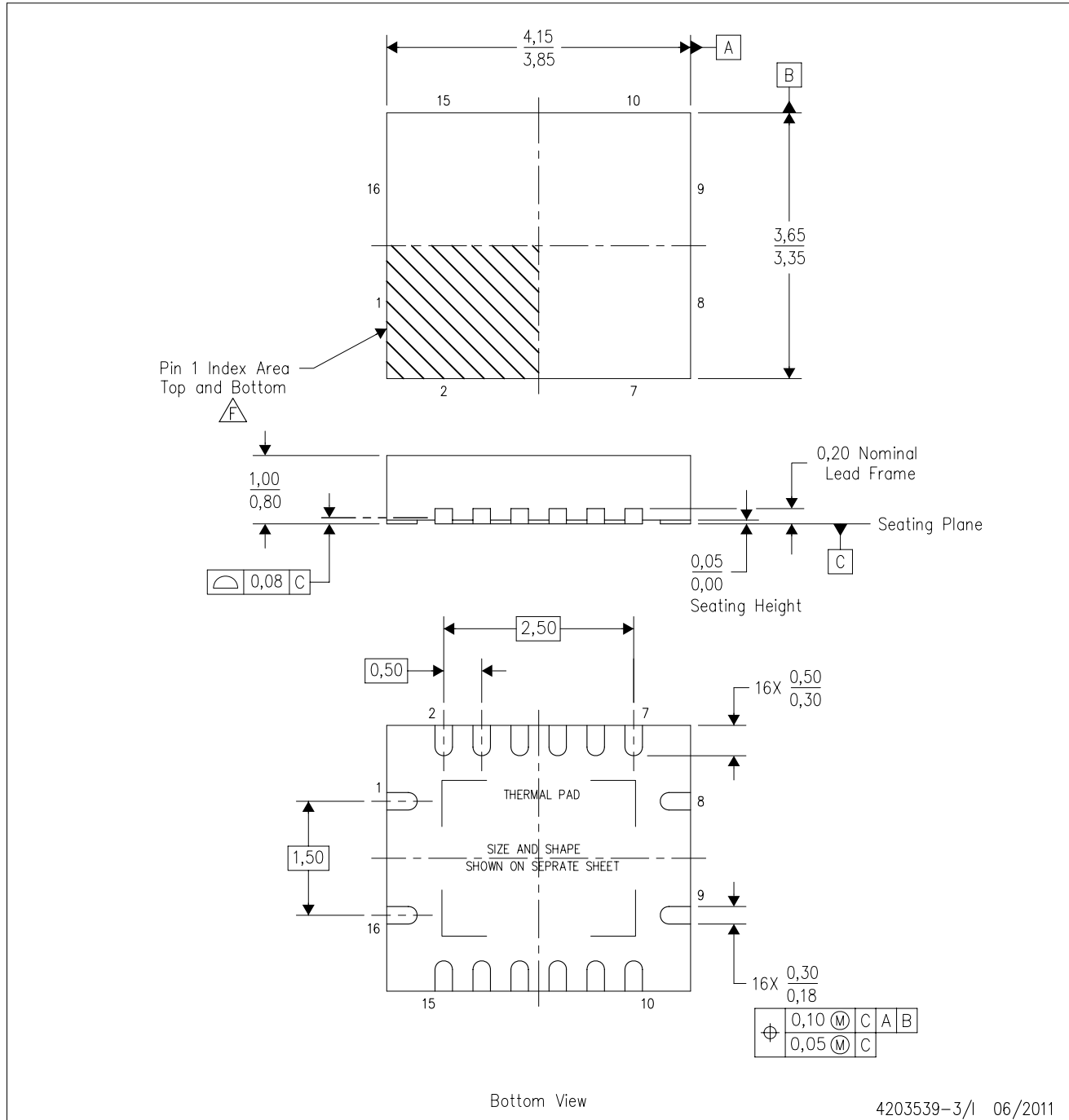
4214846/A 03/2014

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

RGY (R-PVQFN-N16)

PLASTIC QUAD FLATPACK NO-LEAD



- NOTES:
- All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - This drawing is subject to change without notice.
 - QFN (Quad Flatpack No-Lead) package configuration.
 - The package thermal pad must be soldered to the board for thermal and mechanical performance.
 - See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F** Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
- G. Package complies to JEDEC MO-241 variation BA.

RGY (R-PVQFN-N16)

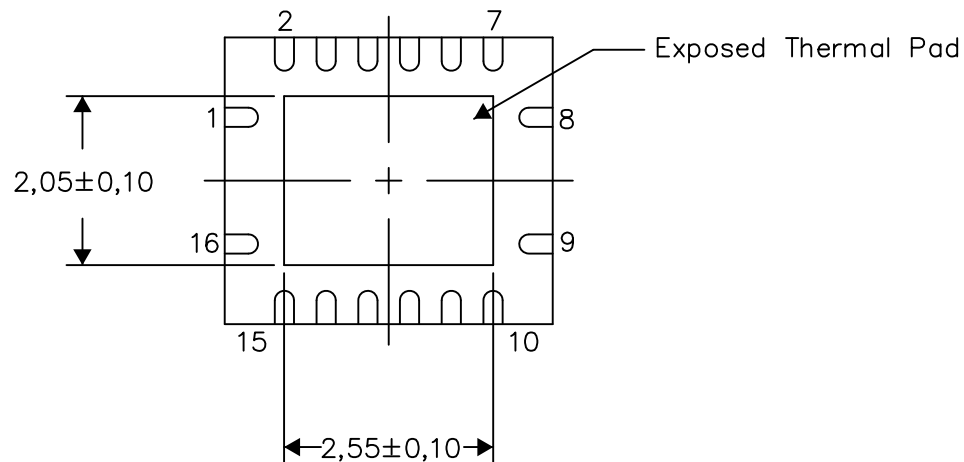
PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.

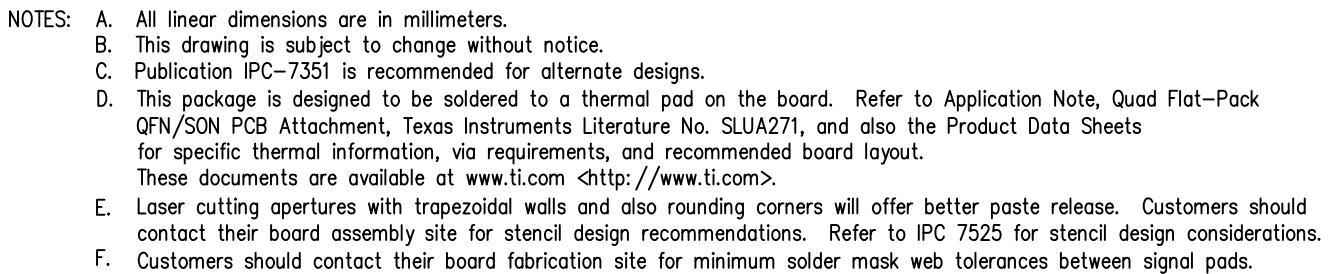


Bottom View

Exposed Thermal Pad Dimensions

4206353-3/P 03/14

NOTE: All linear dimensions are in millimeters



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